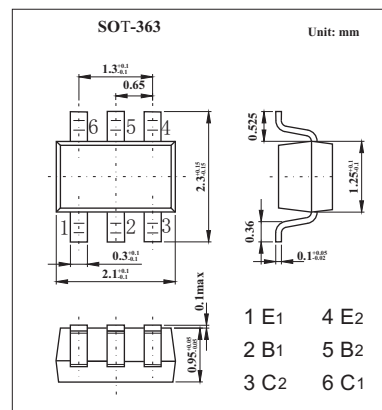
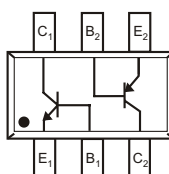


NPN/PNP Complementary Silicon Transistor Array BC847PN

■ Features

- Two internal isolated NPN/PNP Transistors in one package
- For Switching and AF Amplifier Applications
- Ultra-Small Surface Mount Package



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CE0}	45	V
Emitter-Base Voltage	V _{EB0}	6	V
Collector Current -Continuous	I _C	0.1	A
Collector Power Dissipation	P _C	200	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CB0}	I _C = 10 μA, I _E = 0	50			V
Collector-emitter breakdown voltage	V _{(BR)CE0}	I _C = 10mA, I _B = 0	45			V
Emitter-base Breakdown voltage	V _{(BR)EB0}	I _E = 10 μA, I _C = 0	6			V
Collector-base cutoff current	I _{CBO}	V _{CB} = 30 V, I _E = 0			15	nA
Emitter-base cutoff current	I _{EB0}	V _{EB} = 5 V, I _C = 0			15	nA
DC current gain	h _{FE}	V _{CE} = 5 V, I _C = 2 mA	200		450	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 100 mA, I _B = 5mA			0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = 100 mA, I _B = 5mA		0.9		V
Collector output capacitance	C _{ob}	V _{CB} =10V,f=1MHz			6	pF
Transition frequency	f _T	V _{CE} = 5 V, I _C = 10 mA, f = 100 MHz	100			MHz
Noise figure	NF	V _{CE} =5V,I _C =0.2mA,f=1kHz, R _g =2KΩ,Δf=200Hz			10	dB

■ Marking

Marking	7P
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